

TOSHIBA Photocoupler GaAlAs IRED + Photo IC

TLP350

Industrial Inverter
 Inverter for Air Conditioner
 IGBT/Power MOSFET Gate Drive
 IH(Induction Heating)

The TOSHIBA TLP350 consists of a GaAlAs light-emitting diode and an integrated photodetector.

This unit is an 8-lead DIP package.

The TLP350 is suitable for gate driving IGBTs or power MOSFETs.

- Peak output current : $I_O = \pm 2.5A$ (max)
- Guaranteed performance over temperature : -40 to $100^\circ C$
- Supply current : $I_{CC} = 2$ mA (max)
- Power supply voltage: $V_{CC} = 15$ to 30 V
- Threshold input current : $I_{FLH} = 5$ mA (max)
- Switching time (t_{pLH}/t_{pHL}) : 500 ns (max)
- Common mode transient immunity : 15 kV/ μs
- Isolation voltage : 3750 Vrms
- UL Recognized : UL1577,File No.E67349
- Option(D4)

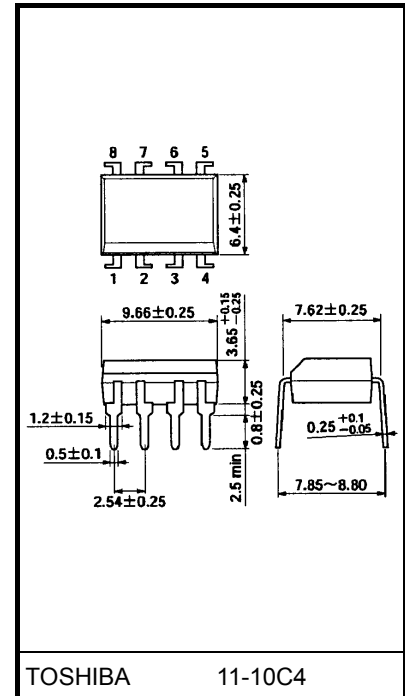
VDE Approved : DIN EN60747-5-2

Maximum Operating Insulation Voltage : 890V_{PK}

Highest Permissible Over Voltage : 6000V_{PK}

(Note):When a EN60747-5-2 approved type is needed, Please designate "Option(D4)"

Unit: mm



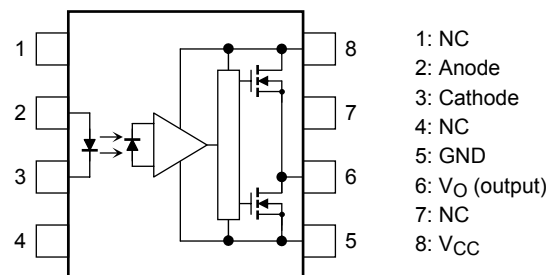
TOSHIBA 11-10C4

Weight: 0.54 g (typ.)

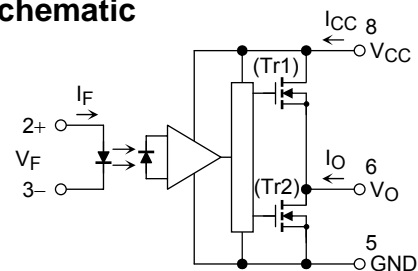
Truth Table

Input	LED	Tr1	Tr2	Output
H	ON	ON	OFF	H
L	OFF	OFF	ON	L

Pin Configuration (top view)



Schematic



A 0.1 μF bypass capacitor must be connected between pins 8 and 5. (See Note 6)

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
LED	Forward current	I_F	20	mA	
	Forward current derating (Ta ≥ 85°C)	$\Delta I_F / \Delta T_a$	-0.54	mA/°C	
	Peak transient forward current (Note 1)	I_{FP}	1	A	
	Reverse voltage	V_R	5	V	
	Junction temperature	T_j	125	°C	
Detector	"H" peak output current	$T_a = -40 \text{ to } 100^\circ\text{C}$ (Note 2)	I_{OPH}	-2.5	A
	"L" peak output current		I_{OPL}	2.5	A
	Supply voltage	$T_a < 95^\circ\text{C}$	V_{CC}	35	V
	Supply voltage Derating	$T_a \geq 95^\circ\text{C}$	V_{CC} / T_a	-1.0	V /
	Junction temperature		T_j	125	°C
	Operating frequency (Note 3)		f	50	kHz
Storage temperature range		T_{stg}	-55 to 125	°C	
Operating temperature range		T_{opr}	-40 to 100	°C	
Lead soldering temperature (10 s) (Note 4)		T_{sol}	260	°C	
Isolation voltage (AC, 1 minute, R.H. ≤ 60%) (Note 5)		BV_S	3750	Vrms	

Note 1: Pulse width $P_W \leq 1 \mu\text{s}$, 300 pps

Note 2: Exponential waveform pulse width $P_W \leq 0.3\mu\text{s}$, $f \leq 15\text{kHz}$

Note 3: Exponential waveform $I_{OPH} \geq -2.0\text{A}$ ($\leq 0.3\mu\text{s}$), $I_{OPL} \leq 2.0\text{A}$ ($\leq 0.3\mu\text{s}$)

Note 4: At 2 mm or more from the lead root.

Note 5: This device is regarded as a two terminal device: pins 1, 2, 3 and 4 are shorted together, as are pins 5, 6, 7 and 8.

Note 6: A ceramic capacitor(0.1 μF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypass may impair the switching property.
The total lead length between capacitor and coupler should not exceed 1 cm.

Recommended Operating Conditions

Characteristic	Symbol	Min	Typ.	Max	Unit
Input current, ON (Note 7)	I_F (ON)	7.5	—	10	mA
Input voltage, OFF	V_F (OFF)	0	—	0.8	V
Supply voltage	V_{CC}	15	—	30	V
Peak output current	I_{OPH}/I_{OPL}	—	—	± 2.0	A
Operating temperature	T_{opr}	-40	—	100	°C

Note 7: Input signal rise time (fall time) < 0.5 μs .

Note 8: If the rising slope of the supply voltage (V_{CC}) for the detector is steep, stable operation of the internal circuits cannot be guaranteed.

Be sure to set 3.0V/ μs or less for a rising slope of the V_{CC} .

Electrical Characteristics (Ta = -40 to 100°C, unless otherwise specified)

Characteristic	Symbol	Test Circuit	Test Conditions	Min	Typ.*	Max	Unit		
Forward voltage	V _F	—	I _F = 10 mA, Ta = 25°C	—	1.6	1.8	V		
Temperature coefficient of forward voltage	ΔV _F /ΔTa	—	I _F = 10 mA	—	-2.0	—	mV/°C		
Input reverse current	I _R	—	V _R = 5 V, Ta = 25°C	—	—	10	μA		
Input capacitance	C _T	—	V = 0, f = 1 MHz, Ta = 25°C	—	45	250	pF		
Output current (Note 9)	"H" Level	I _{OPH}	1	V _{CC} = 30 V, I _F = 5 mA V ₈₋₆ = -3.5 V	—	-1.6	-1.0	A	
				V _{CC} = 15 V, I _F = 5 mA V ₈₋₆ = -7.0 V	—	—	-2.0		
	"L" Level	I _{OPL}	2	V _{CC} = 30 V, I _F = 0 mA V ₆₋₅ = 2.5V	1.0	1.6	—		
				V _{CC} = 15 V, I _F = 0 mA V ₆₋₅ = 7.0V	2.0	—	—		
Output voltage	"H" Level	V _{OH}	3	V _{CC} 1= +15 V V _{EE} 1= -15 V	I _F = 5 mA	11	13.7	—	V
	"L" Level	V _{OL}	4	R _L = 200	V _F = 0.8 V	—	-14.9	-12.5	
Supply current	"H" Level	I _{CCH}	5	V _{CC} = 30 V	I _F = 10 mA	—	1.3	2.0	mA
	"L" Level	I _{CCL}	6	V _O open	I _F = 0 mA	—	1.3	2.0	
Threshold input current	L → H	I _{FLH}	—	V _{CC} = 15V, V _O > 1V, I _O = 0mA	—	1.8	5	mA	
Threshold input voltage	H → L	V _{FHL}	—	V _{CC} = 15V, V _O < 1V, I _O = 0mA	0.8	—	—	V	
Supply voltage	V _{CC}	—	—	—	15	—	30	V	
UVLO threshold	V _{UVLO+}	—	—	V _O > 2.5 V, I _F = 5 mA	11.0	12.5	13.5	V	
	V _{UVLO-}	—	—	—	9.5	11.0	12.0	V	
UVLO hysteresis	UVLO _{HYS}	—	—	—	—	1.5	—	V	

*: All typical values are at Ta = 25°C

Note 9: Duration of I_O : ≤ 50 μs(1PULSE)

Note 10: This product is more sensitive to static electricity (ESD) than the conventional product because of its minimal power consumption design.

General static electricity precautions are necessary for handling this component.

Isolation Characteristics (Ta = 25°C)

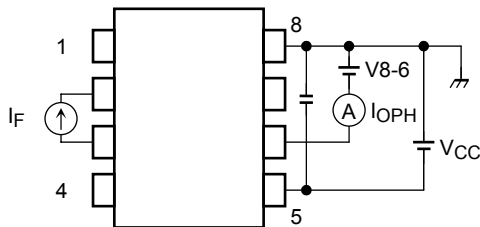
Characteristic	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Capacitance input to output	C _S	V = 0, f = 1MHz (Note5)	—	1.0	—	pF
Isolation resistance	R _S	V _S = 500 V, Ta = 25°C, R.H. ≤ 60% (Note5)	1×10 ¹²	10 ¹⁴	—	Ω
Isolation voltage	BV _S	AC, 1 minute	3750	—	—	V _{rms}
		AC, 1 second, in oil	—	10000	—	V _{rms}
		DC, 1 minute, in oil	—	10000	—	V _{dc}

Switching Characteristics (Ta = -40 to 100°C, unless otherwise specified)

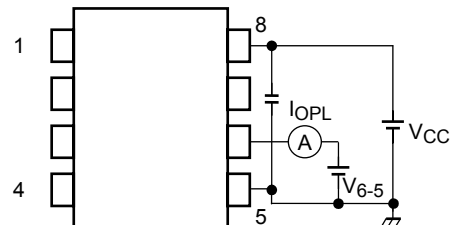
Characteristic	Symbol	Test Circuit	Test Conditions	Min	Typ.*	Max	Unit	
Propagation delay time	L → H	7	V _{CC} = 30 V R _g = 20 Ω C _g = 10 nF	I _F = 0 → 5 mA	50	260	500	ns
	H → L			I _F = 5 → 0 mA	50	260	500	
Switching Time Dispersion between ON and OFF	t _{pHL} - t _{pLH}	7	V _{CC} = 30 V R _g = 20 Ω, C _g = 10 nF	—	—	350	ns	
Output rise time (10-90%)	t _r	7	V _{CC} = 30 V R _g = 20 Ω C _g = 10 nF	I _F = 0 → 5 mA	—	15	—	ns
Output fall time (90-10%)	t _f			I _F = 5 → 0 mA	—	8	—	
Common mode transient immunity at high level output	CM _H	8	V _{CM} = 1000 V _{p-p} Ta = 25°C V _{CC} = 30 V	I _F = 5 mA V _O (min) = 26V	-15000	—	—	V/μs
Common mode transient immunity at low level output	CM _L			I _F = 0 mA V _O (max) = 1V	15000	—	—	

*: All typical values are at Ta = 25°C

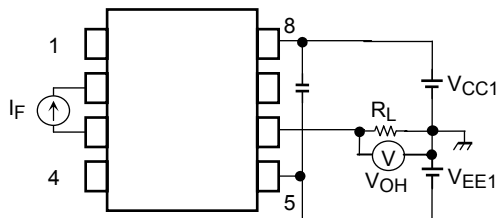
Test Circuit 1: I_{OPH}



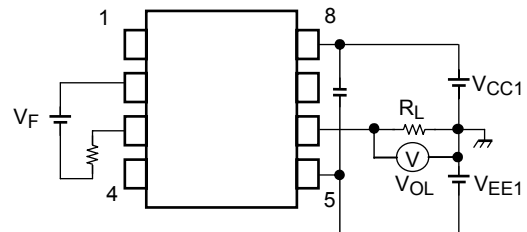
Test Circuit 2: I_{OPL}



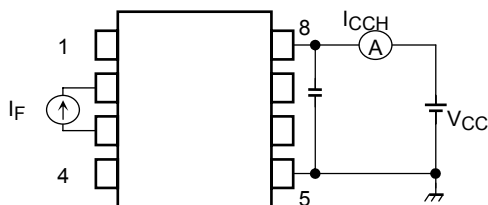
Test Circuit 3: V_{OH}



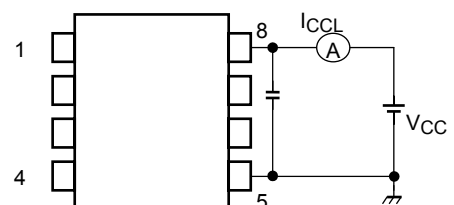
Test Circuit 4: V_{OL}



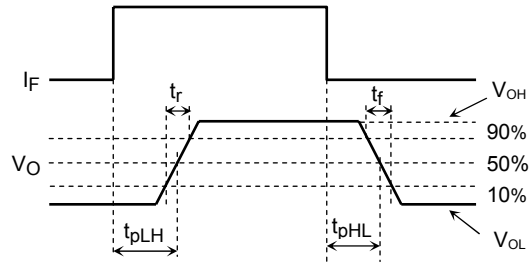
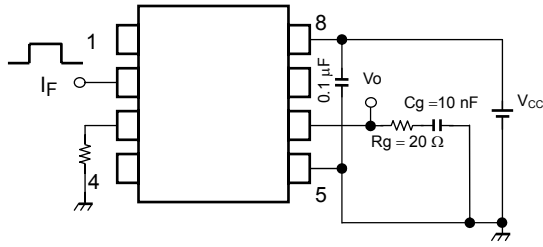
Test Circuit 5: I_{CCH}



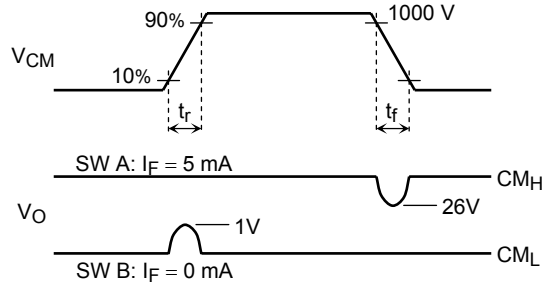
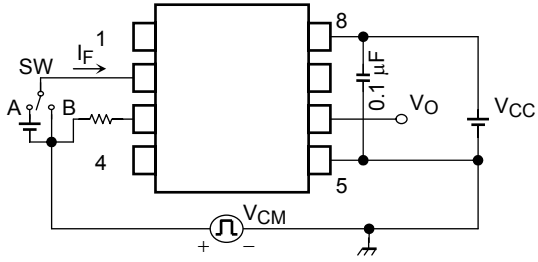
Test Circuit 6: I_{CCL}



Test Circuit 7: t_{pLH} , t_{pHL} , t_r , t_f , PDD

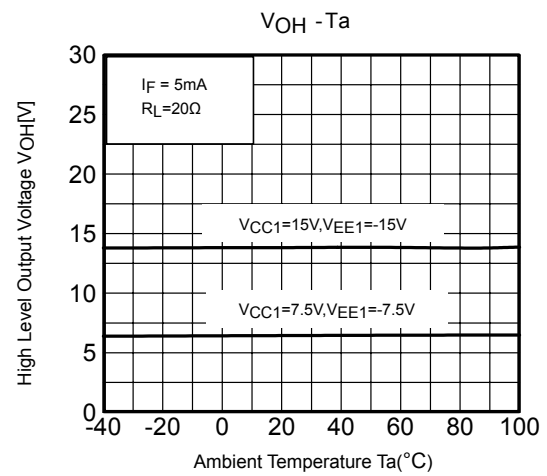
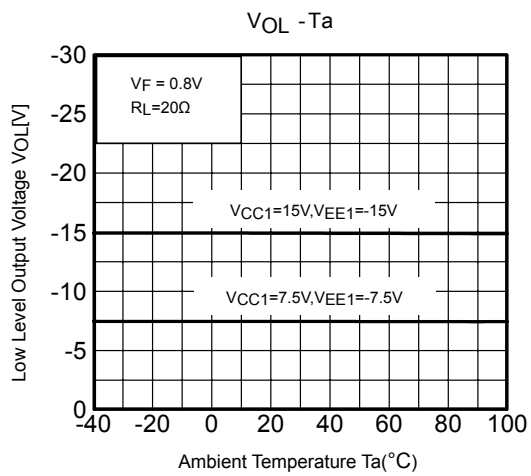
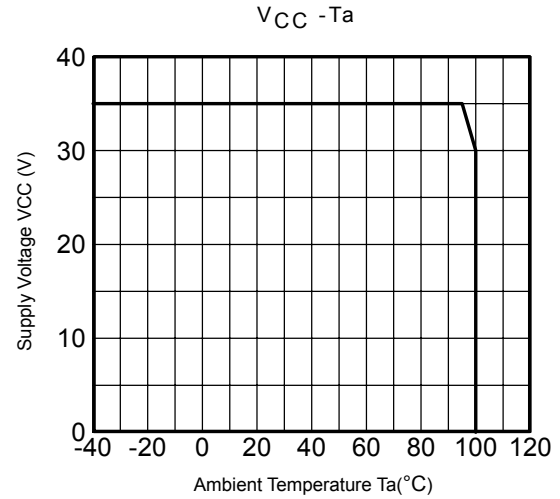
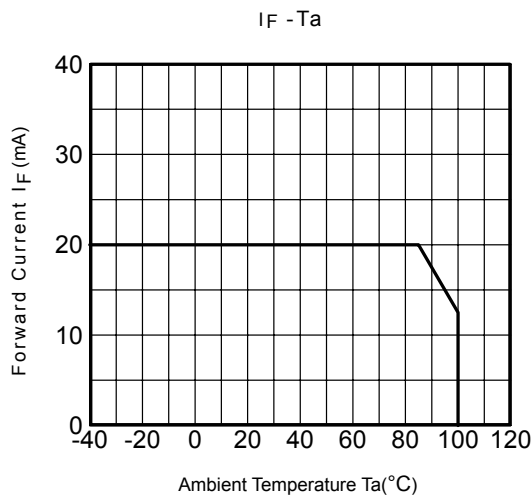
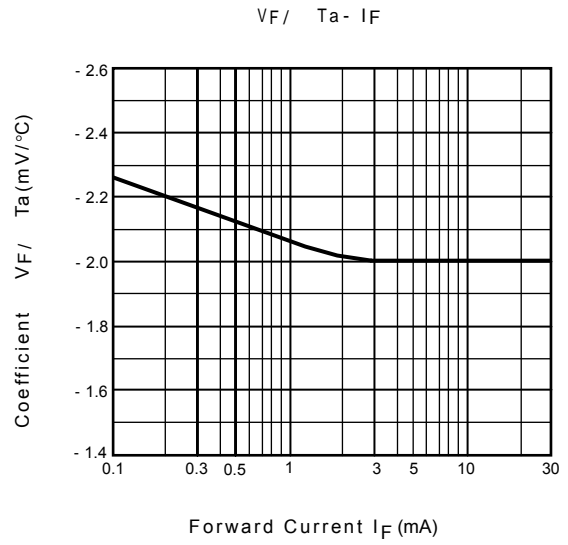
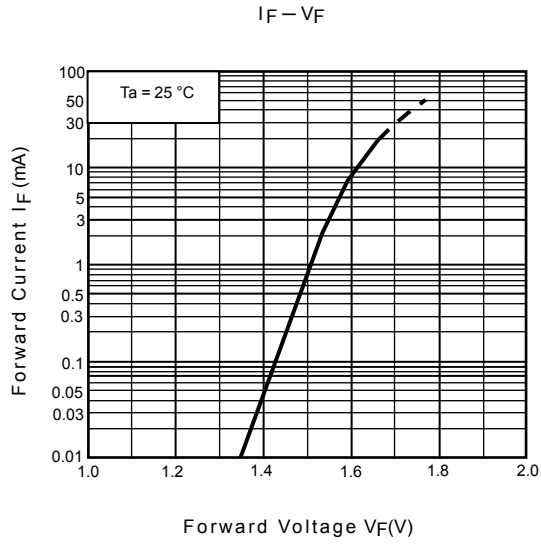


Test Circuit 8: CM_H , CM_L

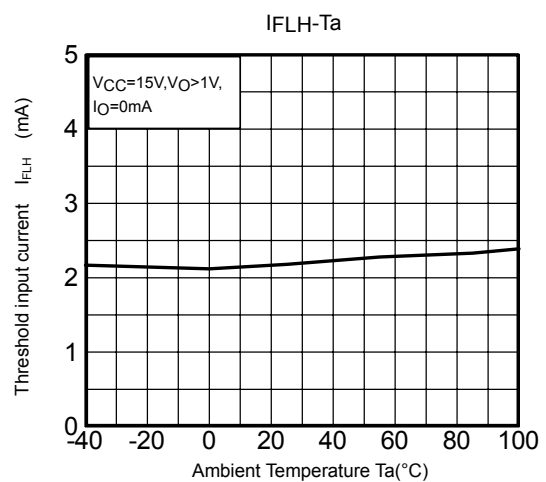
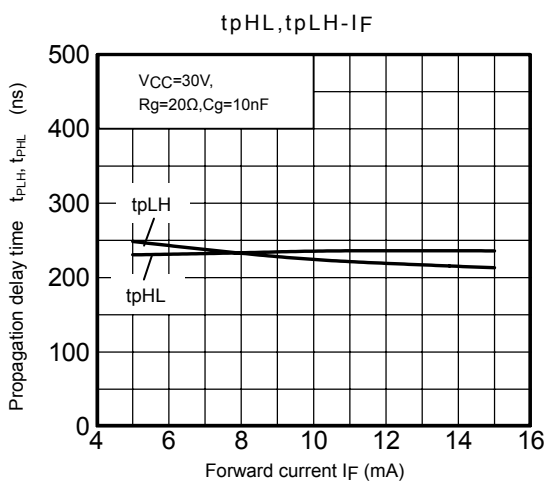
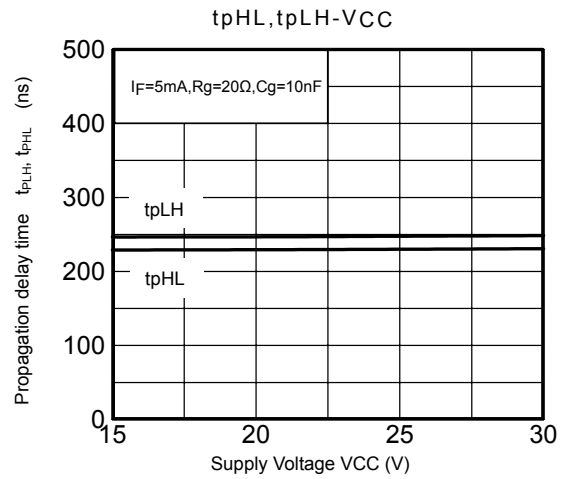
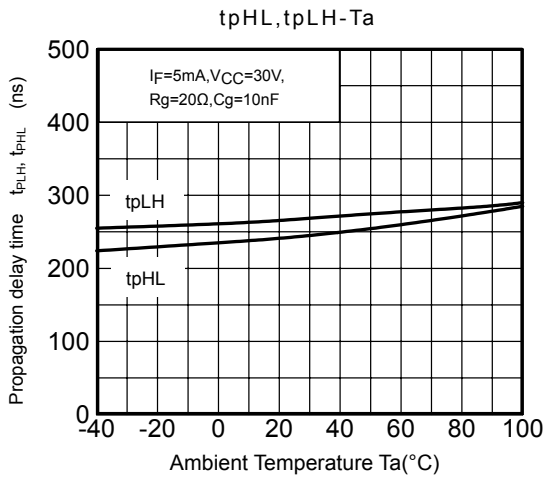
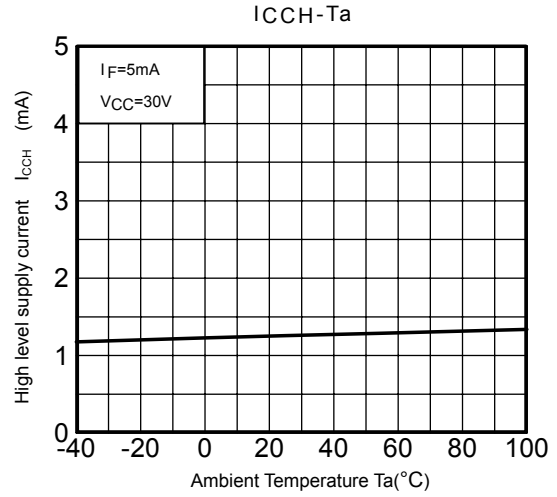
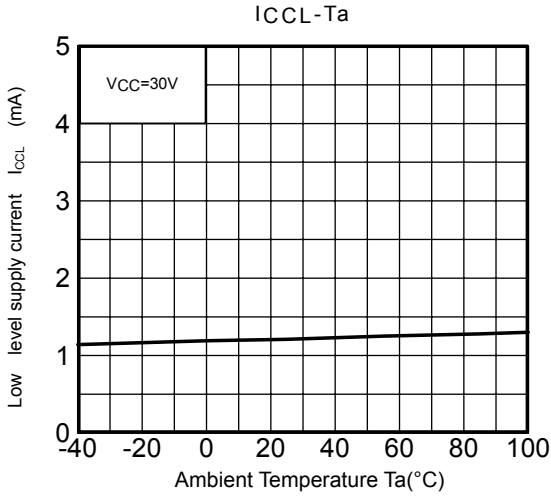


$$CM_L = \frac{800(V)}{t_r(\mu s)} \quad CM_H = \frac{800(V)}{t_f(\mu s)}$$

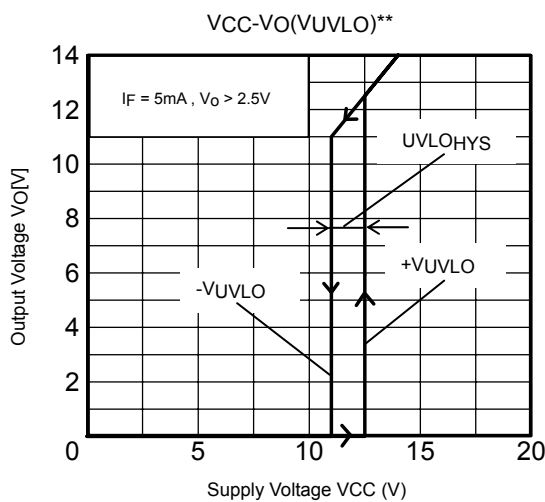
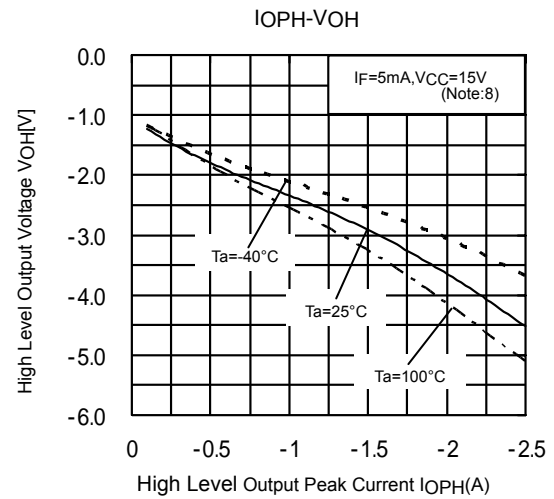
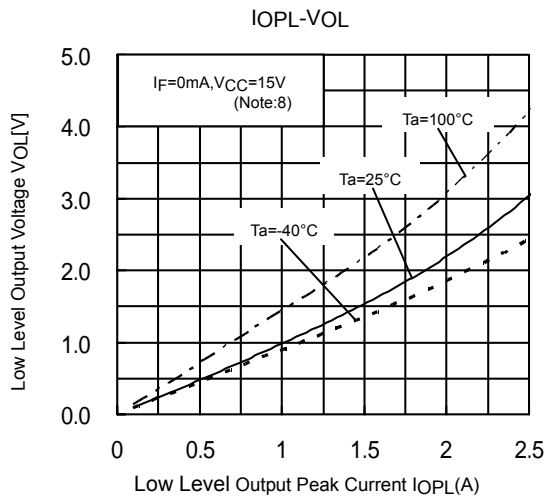
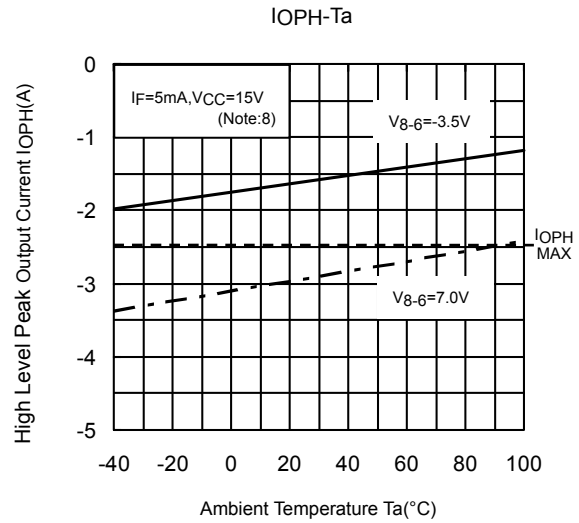
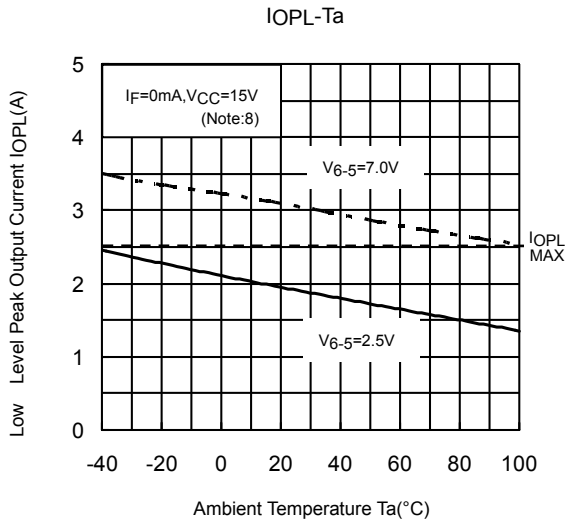
CM_L (CM_H) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.



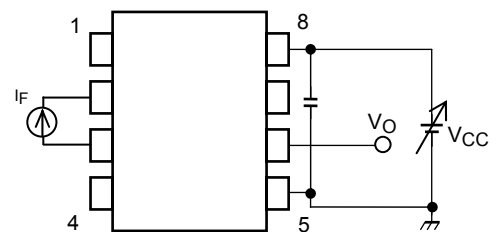
*: The above graphs show typical characteristics.



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**Test Circuit : V_{CC}-V_O(V_{UVLO})



*: The above graphs show typical characteristics.

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